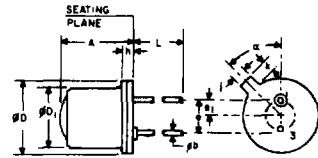


LED55B, LED55C, LED56, LED55BF, LED55CF, LED56F

**Infrared Emitter
Gallium Arsenide Infrared Emitting Diode**

The LED55B-LED55C-LED56 Series are gallium arsenide, light emitting diodes which emit non-coherent, infrared energy with a peak wave length of 940 nanometers. They are ideally suited for use with silicon detectors. The LED55B, LED55C and LED56 devices have a lens which provides a narrow beam angle while the "F" versions have a flat window for a wide beam angle which is useful with external lensing.



LED55B , LED55C , LED56

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A		.255		6.47	
#D	.015	.021	4.07	5.33	
#D	.208	.230	5.31	5.84	
#D1	.180	.188	4.57	4.77	
#	1.00 NOM.		2.54 NOM.		?
#1	.050 NOM.		1.27 NOM.		2
#2		.050		.76	
#3	.031	.044	.79	1.11	
#4	.036	.046	.92	1.16	1
L	1.00		25.4		
d		45°		45°	3

absolute maximum ratings: (25°C unless otherwise specified)

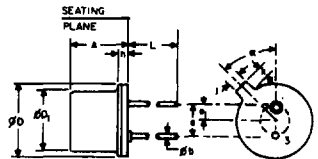
Voltage:
Reverse Voltage V_R 3 volts

Currents:
Forward Current Continuous I_F 100 mA
Forward Current (pw 1 μ sec 200 Hz) I_F 10 A

Dissipations:
Power Dissipation ($T_A = 25^\circ C$)* P_T 170 mW
Power Dissipation ($T_C = 25^\circ C$)** P_T 1.3 W

Temperatures:
Junction Temperature T_J -65°C to +150°C
Storage Temperature T_{STG} -65°C to +150°C
Lead Soldering Time 10 seconds at 260°C

*Derate 1.36 mW/°C above 25°C ambient.
**Derate 10.4 mW/°C above 25°C case.



LED55BF, LED55CF, LED56F

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A		.155		3.93	
#D	.015	.021	4.07	5.33	
#D	.208	.230	5.31	5.84	
#D1	.180	.188	4.57	4.77	
#	1.00 NOM.		2.54 NOM.		2
#1	.050 NOM.		1.27 NOM.		2
#2		.050		.76	
#3	.031	.044	.79	1.11	
#4	.036	.046	.92	1.16	1
L	1.00		25.4		
d		45°		45°	3

electrical characteristics: (25°C unless otherwise specified)

	MIN.	TYP.	MAX.	UNITS
Reverse Leakage Current ($V_R = 3V$)			10	μA
Forward Voltage ($I_F = 100mA$)	V_F	1.4	1.7	V

optical characteristics: (25°C unless otherwise specified)

Total Power Output (note 1)
($I_F = 100mA$)

LED55B-LED55BF	P_O 3.5	mW
LED55C-LED55CF	5.4	mW
LED56 -LED56F	1.5	mW

Peak Emission Wavelength ($I_F = 100mA$) 940 nm

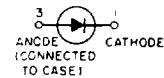
Spectral Shift with Temperature .28 nm/°C

Spectral Bandwidth 50% 60 nm

Rise Time 0-90% of Output 1.0 μ sec

Fall Time 100-10% of Output 1.0 μ sec

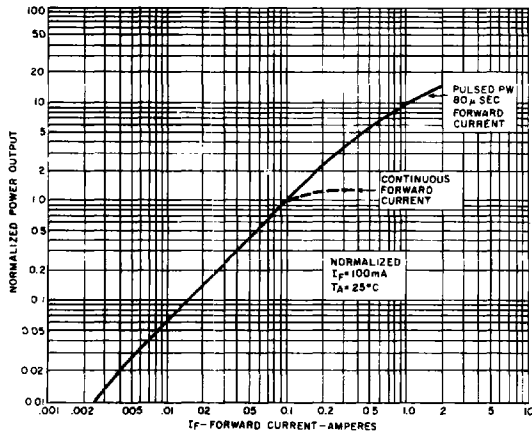
Note 1: Total power output, P_O , is the total power radiated by the device into a solid angle of 2π steradians.



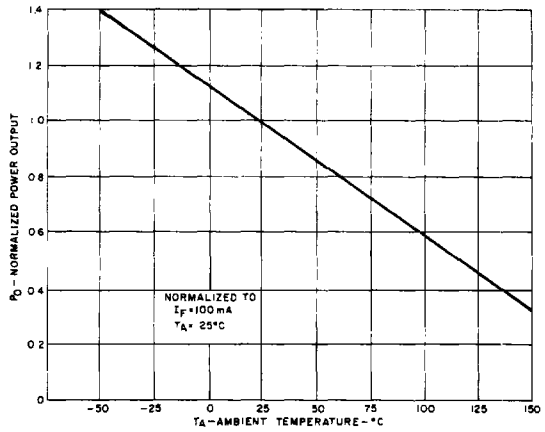
1. Measured from maximum diameter of device.
2. Leads having max. diameter .021" (.533mm) measured in gaging plane .054" \pm .001" \pm .000 (.137 + .025 - .000mm) below the reference plane of the device shall be within .007" (1.778mm) their true position relative to a maximum width tab.
3. From centerline tab.

LED55B, LED55C, LED56, LED55BF, LED55CF, LED56F

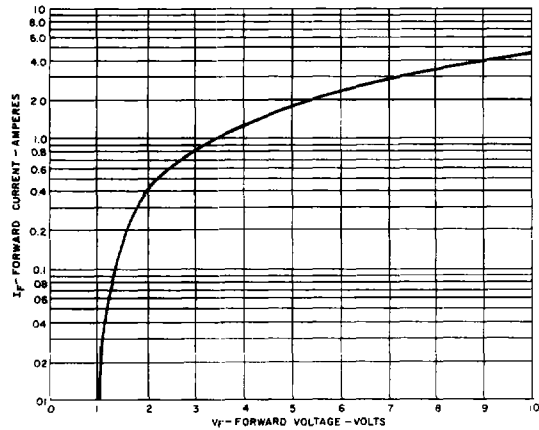
TYPICAL CHARACTERISTICS



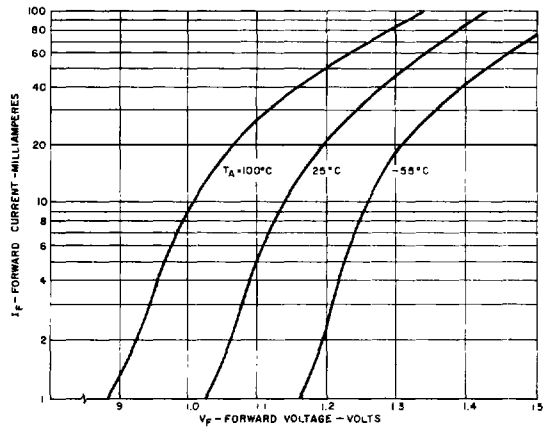
1. POWER OUTPUT VS. INPUT CURRENT



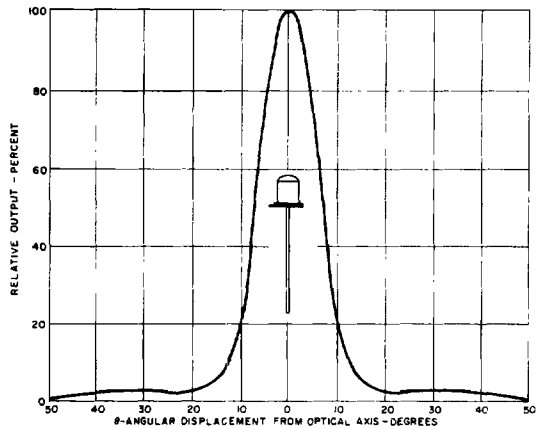
2. POWER OUTPUT VS. TEMPERATURE



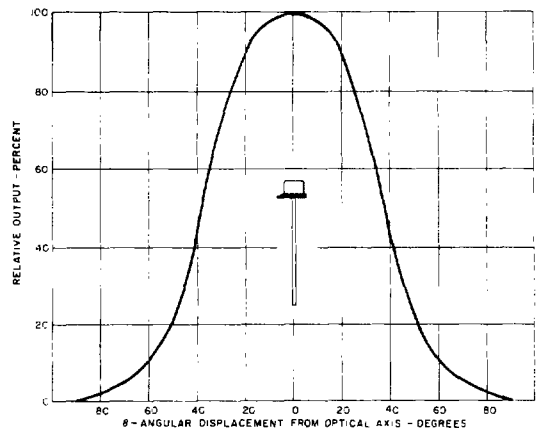
3. LED 55B, 55C, 56, 55BF, 55CF, 56F FORWARD VOLTAGE VS. FORWARD CURRENT



4. FORWARD VOLTAGE VS. FORWARD CURRENT



5. LED 55B, 55C, 56 TYPICAL RADIATION PATTERN



6. LED 55BF, 55CF, 56F TYPICAL RADIATION PATTERN

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